

KSC5086

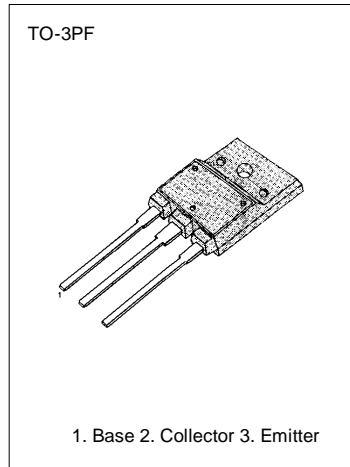
**NPN TRIPLE DIFFUSED
PLANAR SILICON TRANSISTOR**

**HIGH DEFINITION COLOR DISPLAY
HORIZONTAL DEFLECTION OUTPUT
(DAMPER DIODE BUILT IN)**

- High Collector -Base Voltage ($V_{CBO}=1500V$)
- High Speed Switching ($t_f=0.1\mu\text{sec Typ}$)

ABSOLUTE MIXIMUM RATING

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V_{CBO}	1500	V
Collector Emitter Voltage	V_{CEO}	800	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	7	A
Collector Current (Pulse)	I_C	1.6	A
Collector Dissipation ($T_C=25^\circ\text{C}$)	P_C	5.0	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ 150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current ($V_{BE}=0$)	I_{CES}	$V_{CE} = 1400V, R_{BE} = 0$			1	mA
Collector Cutoff Current	I_{CBO}	$V_{CB}=800V, I_E=0$			10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4V, I_C = 0$	40		200	mA
Base Emitter Breakdown Voltage	V_{EBO}	$I_E = 250\text{mA}, I_C = 0$	6			V
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 1.0A$	8			
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 5A, I_B = 1.2A$			5	V
Base Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 5A, I_B = 1.2A$			1.5	V
Damper Diode Turn On Voltage	V_F	$I_F = 6A$			2	V
Storage Time	t_F	$V_{CC} = 200V, I_C = 4A$ $I_{B1} = 0.8A, I_{B2} = -1.6A$ $R_L = 50\Omega$			0.2	μs

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